

PATENT ABSTRACTS OF JAPAN

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(21)Application number : 07-079644 (71)Applicant : TONEN CORP

(22)Date of filing : 10.03.1995 (72)Inventor : TASHIRO YUJI
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(54) HEAT-RESISTANT FILM AND ITS PRODUCTION

(57)Abstract:

PURPOSE: To obtain a highly heat-resistant film by forming a silicon copolymer comprising structural units represented by specific formulas into a film.

CONSTITUTION: A silicon copolymer having structural units represented by formulas I to V (wherein R1 and R2 are each alkyl, cycloalkyl, etc.; R3 is alkylene, alkenylene, etc.; II, m, and n are each 1 or higher; and o and p are each 0 or a positive integer) is obtd. by dissolving a diamine (e.g. p-phenylenediamine) in a solvent (e.g. xylene) in an N2 atmosphere, dissolving a disilyl compd. [e.g. an organohydrodihalosilane, an organodihalosilane, or 1,4-bis(dimethylchlorosilyl)benzene] in the soln. under heating, adding an amine to the resulting soln. to capture hydrochloric acid generated by the reaction, cooling the soln. to about 30°C or lower, adding NH3 to react it with unreacted halogenosilane, removing unreacted NH3 after the reaction, filtering the soln. under pressure, and removing the solvent. The copolymer is formed into a film and cured at 200-500°C in an N2 atmosphere to give a low-birefringence film having a refractive index of 1.45 or higher.

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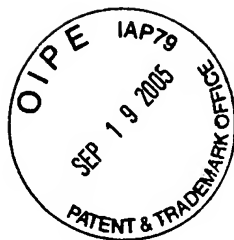
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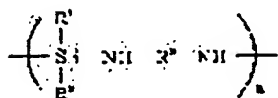
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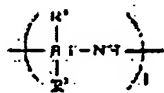


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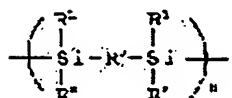
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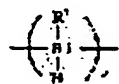
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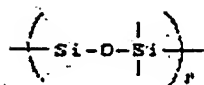
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III



IV



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